WHAT IS CLAIMED IS:

- 1. An apparatus, comprising,
- 2 a substrate having a surface;
- an organic field-effect transistor located adjacent said
- 4 surface of said substrate, said transistor comprising a gate, a
- 5 channel, a source electrode, and a drain electrode; and
- 6 wherein said channel comprises a densified layer of
- 7 organic molecules with conjugated multiple bonds, axes of said
- 8 organic molecules being oriented substantially normal to said
- 9 surface.
- 2. The apparatus of claim 1, wherein said densified layer of
- organic molecules has a surface density of at least about 7
- 3 molecules/nm².
- 3. The apparatus of claim 1, wherein said densified layer is
- 2 defined by said organic molecules having an average separation of
- 3 less than about 3.8 Angstroms.
- 4. The apparatus of claim 1, wherein said densified layer is
- defined by said organic molecules having a uniform orientation that
- 3 provides a polarization ratio of greater than about 1.

- 5. The apparatus of claim 4, wherein said uniform orientation is substantially coincident in a direction of current flow between said source and drain electrodes.
- 6. The apparatus of claim 1, wherein said substrate comprises an elastomer, wherein said elastomer has a glass transition temperature (T_G) of less than about 30°C.
- 7. The apparatus of claim 6, wherein said elastomer is an alkyl-substituted polysiloxane.
- 8. The apparatus as recited in Claim 6, wherein said organic molecules have substantially coplanar aromatic groups.
- The apparatus as recited in Claim 1, wherein said organic
 molecules are linear organic molecules.
- The apparatus as recited in Claim 1, wherein said organic
 molecules are covalently bonded to said surface.
 - 11. The apparatus as recited in Claim 1, wherein said channel has a field effect mobility of at least about $10^{-4}~\rm cm^2~V^{-1}~s^{-1}$.

- 12. A method comprising,
- providing a substrate; and
- forming a channel for an organic field-effect transistor,
- 4 comprising:
- 5 expanding said substrate from an original
- 6 configuration to increase a dimension of said substrate to an
- 7 expanded dimension;
- 8 forming a layer of organic molecules with conjugated
- 9 multiple bonds on said substrate while in said expanded dimension;
- 10 and
- 11 returning said substrate to substantially said
- 12 original configuration.
 - 13. The method of Claim 12, further including forming a gate,
 - 2 a source electrode, and a drain electrode of said organic field-
 - 3 effect transistor.
 - 14. The method of Claim 12, wherein said substrate is a first
 - 2 substrate, and said method further includes forming a gate, a
 - 3 source electrode, and a drain electrode of said organic field-
 - 4 effect transistor on a second substrate and positioning said
- 5 channel between said source and drain electrode and proximate said
- 6 gate by coupling said first and second substrates together.

- 15. The method of claim 12, wherein said expanding comprises2 heating at least a portion of said substrate.
- 16. The method of claim 12, wherein said expanding comprises
 mechanically stretching a portion of said substrate in a lateral
 dimension substantially coincident with a direction of current flow
 between said source and drain electrodes.
- 17. The method of claim 12, wherein said expanded dimension is at least about 10 percent longer than an equivalent portion of said substrate in said original configuration.
- 18. The method of claim 12, wherein returning comprises
 2 relaxing said expanded dimension to substantially said original
 3 configuration in a direction substantially coincident with a
 4 direction of current flow between said source and drain electrodes.
- 19. The method of claim 12, wherein forming said layer of organic molecules comprises covalently bonding an end of said organic molecules to said substrate.
 - 20. The method of claim 12, wherein said channel has a surface density of said organic molecules at least 10 percent

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- 3 greater than a surface density of said organic molecules formed on
- 4 said substrate in said original configuration.